



Excellence in Electronics

TYPE 1N302 (CK737)

The 1N302 is a hermetically sealed silicon junction diode designed for general purpose applications and providing extreme stability, wide temperature range, high back resistance (100 megohms or more), and high ratio of back to forward resistance. The flexible terminal leads may be soldered or welded directly to the terminals of circuit components without the use of sockets. Standard inline subminiature sockets may be used by cutting the leads to a suitable length.

MECHANICAL DATA

CASE: Metal and Glass

BASE: None (0.016" tinned dumet wire. Length: 1.0" min. Spacing: 0.080" center-to-center)

TERMINAL CONNECTIONS: (Black Dot is adjacent to Cathode Terminal)

MOUNTING POSITION: Any

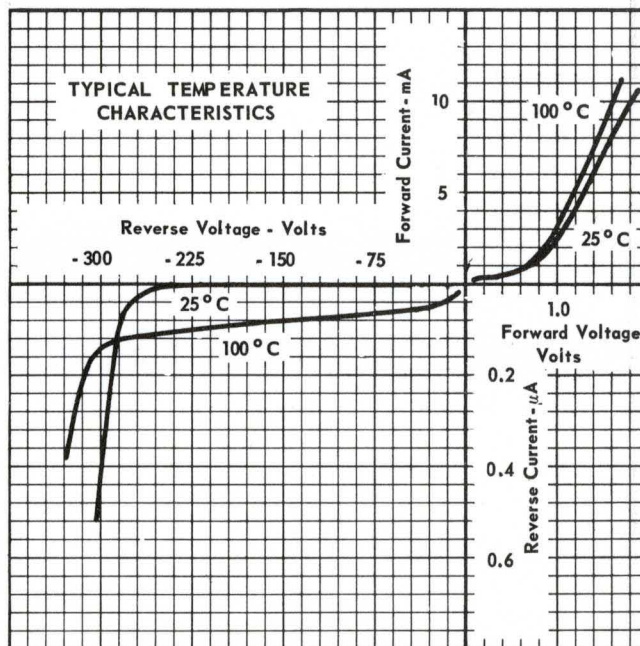
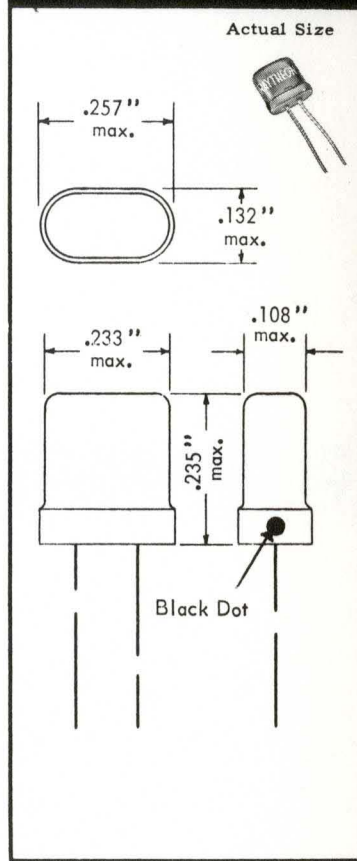
ELECTRICAL DATA

RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)

Peak Inverse Voltage	225 volts
Continuous Inverse Voltage	215 volts
Average Rectified Current	25 ma.
Average Rectified Current (100°C)	8 ma.
Peak Rectified Current	80 ma.
Surge Current (for 1 sec.)	250 ma.
Ambient Temperature Range	-55 to +150 °C
Dissipations at:	
25°C	150 mw.
65°C	60 mw.
100°C	20 mw.
150°C	10 mw.

CHARACTERISTICS:

	100°C	25°C
Maximum Inverse Current at -10 volts	.2	0.01 µa.
Maximum Inverse Current at -200 volts		0.2 µa.
Minimum Forward Current at +1.0 volt		1.0 ma.



Tentative Data

RAYTHEON MANUFACTURING COMPANY RECEIVING AND CATHODE RAY TUBE OPERATIONS